

SSM3K12T

Unit: mm

- Small Package
- Low ON-resistance : $R_{on} = 95 \text{ m}\Omega$ (max) (@ $V_{GS} = 10 \text{ V}$)
: $R_{on} = 145 \text{ m}\Omega$ (max) (@ $V_{GS} = 4.5 \text{ V}$)
- High speed : $t_{on} = 21 \text{ ns}$
: $t_{off} = 16 \text{ ns}$

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

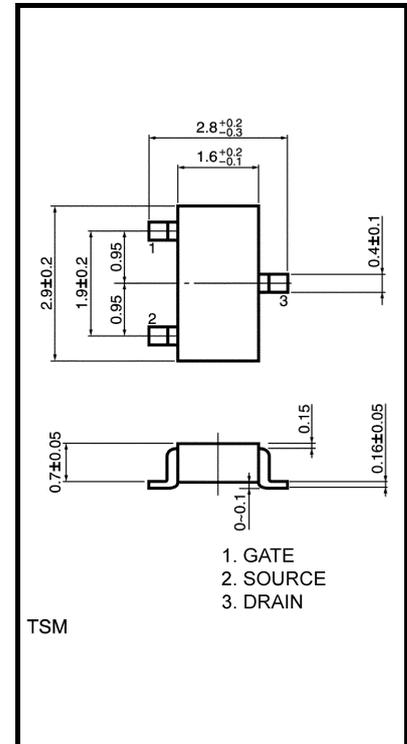
Characteristic	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	30	V
Gate-Source voltage	V_{GS}	± 20	V
Drain current	DC	I_D	3.0
	Pulse	I_{DP} (Note 2)	6.0
Drain power dissipation ($T_a = 25^\circ\text{C}$)	P_D (Note 1)	0.7	W
	$t = 10 \text{ s}$	1.25	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the TY Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board
($25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ t}$, Cu pad: 645 mm^2)

Note 2: The pulse width limited by max channel temperature.



Weight: 10 mg (typ.)

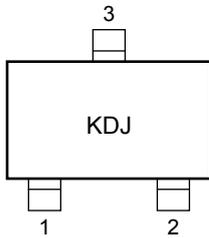
Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

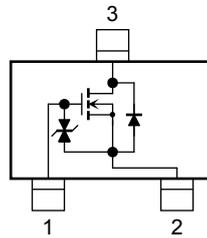
The Channel-to-Ambient thermal resistance $R_{th(ch-a)}$ and the drain power dissipation P_D vary according to the board material, board area, board thickness and pad area, and are also affected by the environment in which the product is used. When using this device, please take heat dissipation fully into account.

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Marking



Equivalent Circuit



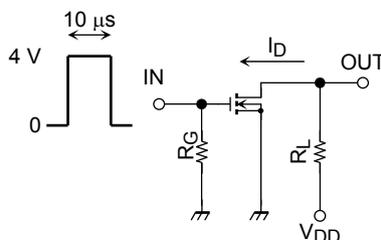
Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0$	—	—	± 1	μA
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1\text{ mA}, V_{GS} = 0$	30	—	—	V
Drain Cut-off current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0$	—	—	1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 5\text{ V}, I_D = 0.1\text{ mA}$	1.1	—	1.8	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 5\text{ V}, I_D = 1.5\text{ A}$ (Note 3)	1.8	3.2	—	S
Drain-Source ON resistance	$R_{DS(ON)}$	$I_D = 1.5\text{ A}, V_{GS} = 10\text{ V}$ (Note 3)	—	78	95	m Ω
		$I_D = 1.5\text{ A}, V_{GS} = 4.5\text{ V}$ (Note 3)	—	117	145	
		$I_D = 1.5\text{ A}, V_{GS} = 4.0\text{ V}$ (Note 3)	—	135	175	
Total gate charge	Q_g	$V_{DD} = 24\text{ V}, I_D = 3\text{ A}, V_{GS} = 4\text{ V}$	—	2.6	—	nC
Input capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	120	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 15\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	20	—	pF
Output capacitance	C_{oss}	$V_{DS} = 15\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	68	—	pF
Switching time	Rise time	t_r	—	13	—	ns
	Turn-on time	t_{on}	—	21	—	
	Fall time	t_f	$V_{DD} = 15\text{ V}, I_D = 1.5\text{ A}$		—	
	Turn-off time	t_{off}	$V_{GS} = 0\sim 4\text{ V}, R_G = 10\ \Omega$		—	

Note 3 : Pulse test

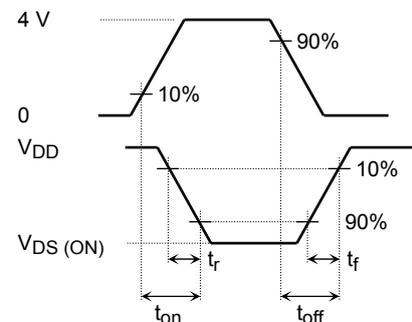
Switching Time Test Circuit

(a) Test circuit



$V_{DD} = 15\text{ V}$
 $R_G = 10\ \Omega$
 $D.U. \leq 1\%$
 $V_{IN}: t_r, t_f < 5\text{ ns}$
 Common source
 $T_a = 25^\circ\text{C}$

(b) V_{IN}



(c) V_{OUT}

Precaution

V_{th} can be expressed as voltage between gate and source when low operating current value is $I_D = 100\ \mu\text{A}$ for this product. For normal switching operation, $V_{GS(ON)}$ requires higher voltage than V_{th} and $V_{GS(OFF)}$ requires lower voltage than V_{th} .

(relationship can be established as follows: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$)

Please take this into consideration for using the device.